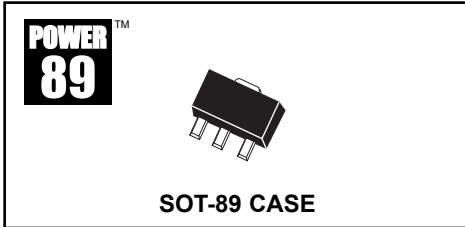


CXT3150
SURFACE MOUNT
NPN SILICON POWER TRANSISTOR



CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXT3150 type is a NPN Silicon Power Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high current, high gain, fast switching applications.

MARKING CODE: FULL PART NUMBER

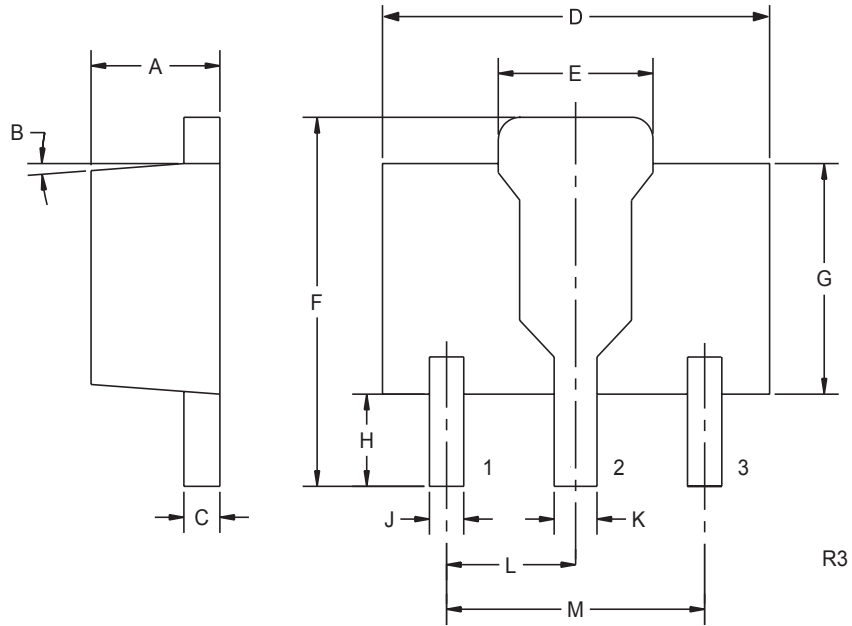
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	7.0	V
Collector Current	I_C	5.0	A
Base Current	I_B	1.0	A
Power Dissipation	P_D	1.2	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	104	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=50\text{V}$			1.0	μA
I_{EBO}	$V_{EB}=7.0\text{V}$			1.0	μA
BV_{CEO}	$I_C=10\text{mA}$	25			V
$V_{CE(SAT)}$	$I_C=3.0\text{A}, I_B=150\text{mA}$			0.35	V
$V_{CE(SAT)}$	$I_C=4.0\text{A}, I_B=200\text{mA}$			0.50	V
$V_{BE(SAT)}$	$I_C=3.0\text{A}, I_B=150\text{mA}$			1.10	V
$V_{BE(SAT)}$	$I_C=4.0\text{A}, I_B=200\text{mA}$			1.40	V
h_{FE}	$V_{CE}=2.0\text{V}, I_C=500\text{mA}$	250		550	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=2.0\text{A}$	150			
h_{FE}	$V_{CE}=2.0\text{V}, I_C=5.0\text{A}$	50			
f_T	$V_{CE}=6.0\text{V}, I_C=50\text{mA}, f=200\text{MHz}$		150		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$			50	pF

SOT-89 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) EMITTER
- 2) COLLECTOR
- 3) BASE

**MARKING CODE:
FULL PART NUMBER**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.016	0.018	0.40	0.46
D	0.173	0.185	4.40	4.70
E	0.070	0.074	1.79	1.87
F	0.146	0.177	3.70	4.50
G	0.094	0.106	2.40	2.70
H	0.028	0.051	0.70	1.30
J	0.015	0.019	0.38	0.48
K	0.019	0.023	0.48	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R3)